

GSMDP4960

40V N-Channel MOSFETs

Product Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

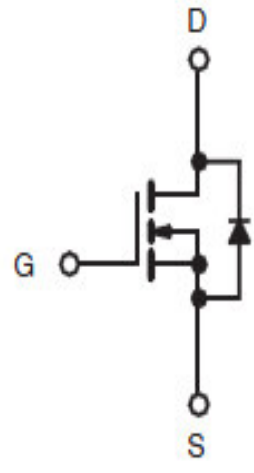
- 40V, 150A, $R_{DS(ON)}=3.8m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- TO-220 package design

Applications

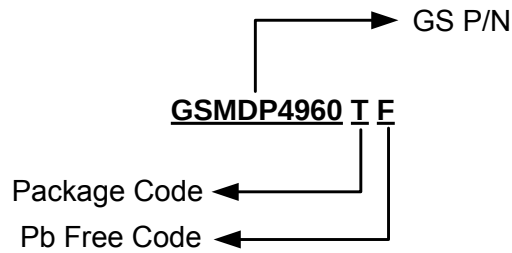
- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Packages & Pin Assignments

GSMDP4960TF (TO-220)	
 Top View	
Pin	Description
1	Gate
2	Drain
3	Source

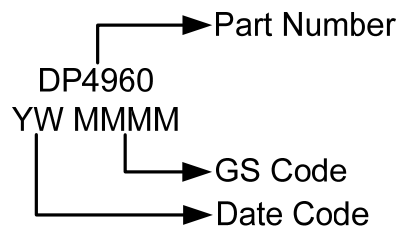


Ordering Information



Part Number	Package	Quantity Tube
GSMDP4960TF	TO-220	50 PCS

Marking Information



Absolute Maximum Ratings

T_C=25°C Unless otherwise noted

Symbol	Parameter		Rating	Units
V _{DS}	Drain-Source Voltage		40	V
V _{GS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C =25°C	150	A
		T _C =100°C	95	
I _{DM}	Pulsed Drain Current (Note 1)		600	A
EAS	Single Pulse Avalanche Energy (Note 2)		312	mJ
IAS	Single Pulse Avalanche Current (Note 2)		79	A
P _D	Power Dissipation (T _C =25°C)		166	W
	Power Dissipation (Derate above 25°C)		1.33	W/°C
T _J	Operating Junction Temperature Range		-55 to +150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient		62	°C/W
R _{θJC}	Thermal Resistance-Junction to Case		0.75	°C/W

Note 1: Repetitive Rating: Pulsed width limited by maximum junction temperature.

Note 2: V_{DD}=25V, V_{GS}=10V, L=0.1mH, IAS=79A, Starting T_J=25°C.

Electrical Characteristics

T_J=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D =250uA	40			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25℃, I _D =1mA		0.03		V/℃
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250uA	1.2	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			-5		mV/℃
I _{GSS}	Gate Leakage Current	V _{DS} =0V,V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V,V _{GS} =0V			1	uA
		V _{DS} =32V,V _{GS} =0V, T _J =125℃			10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			150	A
I _{SM}	Pulsed Source Current (Note 3)				300	
R _{DS(on)}	Drain-Source On-Resistance (Note 3)	V _{GS} =10V,I _D =25A		3.1	3.8	mΩ
		V _{GS} =4.5V,I _D =12A		4.0	5.0	mΩ
g _{FS}	Forward Transconductance	V _{DS} =10V,I _D =2A		16		S
V _{SD}	Diode Forward Voltage (Note 3)	V _{GS} =0V,I _S =1A			1	V
Dynamic						
Q _g	Total Gate Charge (Note 3,4)	V _{DS} =20V,V _{GS} =4.5V, I _D =10A		44.4	80	nC
Q _{gs}	Gate-Source Charge (Note 3,4)			9.6	18	
Q _{gd}	Gate-Drain Charge (Note 3,4)			16	30	
C _{iss}	Input Capacitance	V _{DS} =25V,V _{GS} =0V, f=1MHz		4940	7800	pF
C _{OSS}	Output Capacitance			425	800	
C _{rss}	Reverse Transfer Capacitance			170	330	
t _{d(on)}	Turn-On Time (Note 3,4)	V _{DD} =20V,I _D =1A, V _{GS} =10V,R _G =6Ω		28	50	ns
t _r				3.2	6.5	
t _{d(off)}	Turn-Off Time (Note 3,4)			89	160	
t _f				14	28	
R _g	Gate Resistance	V _{DS} =0V,V _{GS} =0V, f=1MHz		1.4	2.8	Ω

Note 3: The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.

Note 4: Essentially independent of operating temperature.

Typical Performance Characteristics

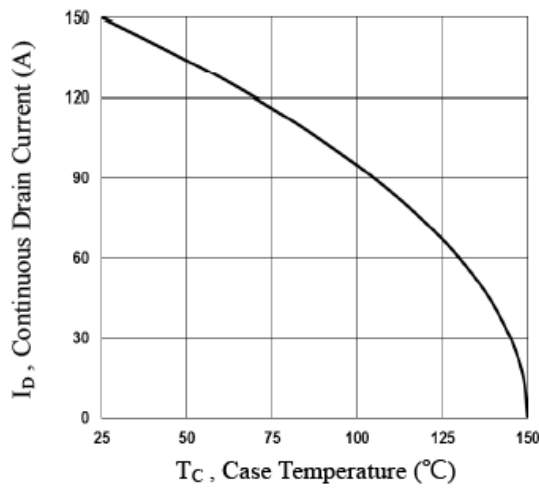


Fig.1 Continuous Drain Current vs. T_c

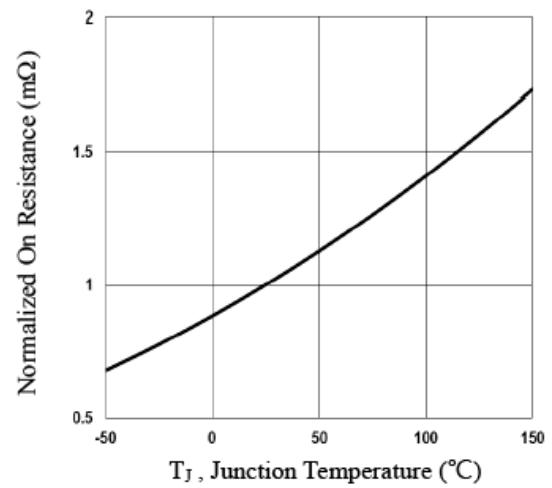


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

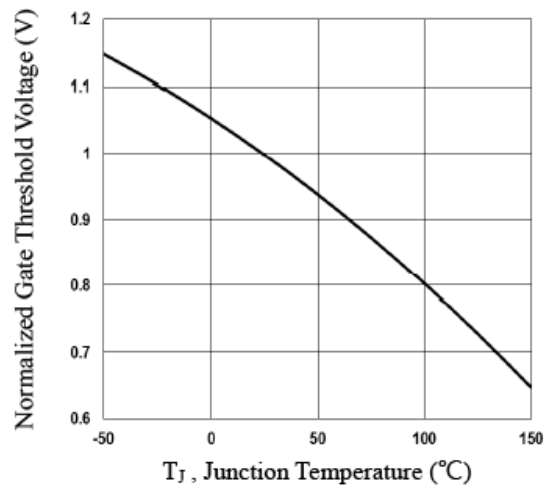


Fig.3 Normalized V_{th} vs. T_j

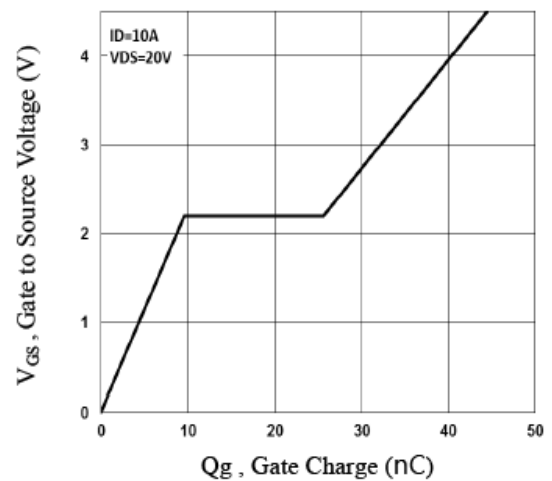


Fig.4 Gate Charge Waveform

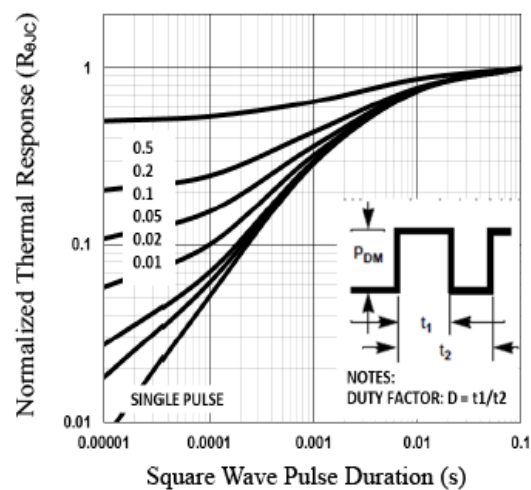


Fig.5 Normalized Transient Impedance

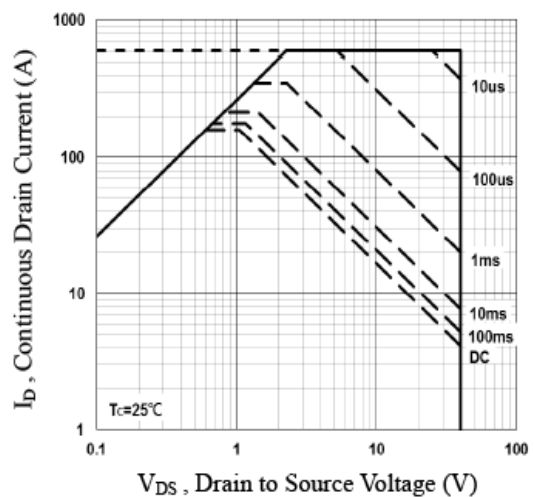
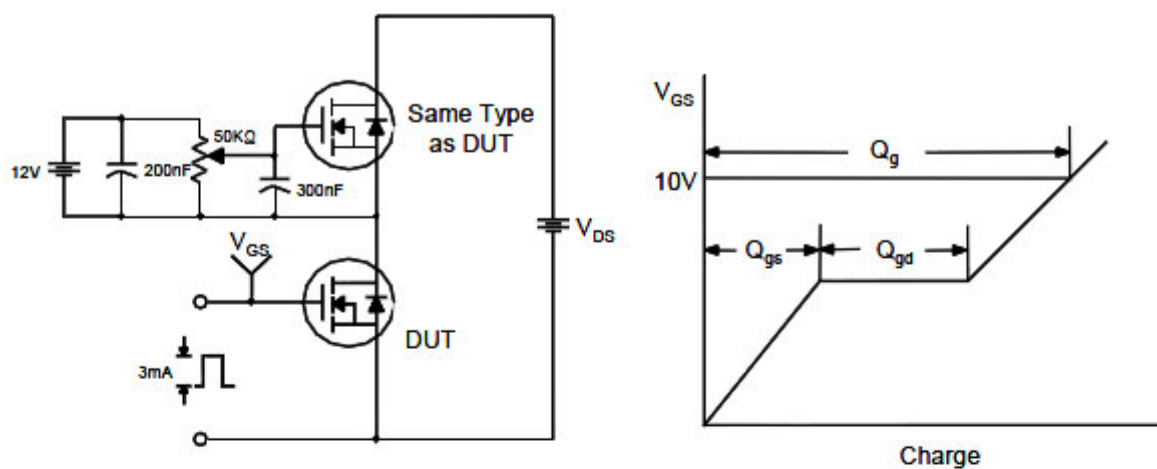


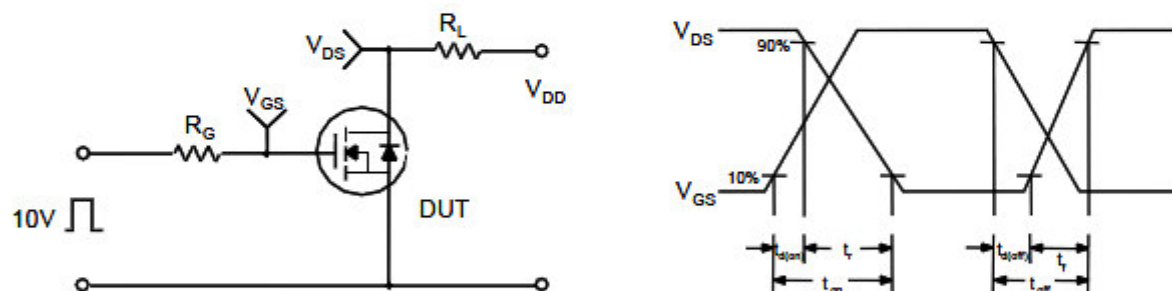
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

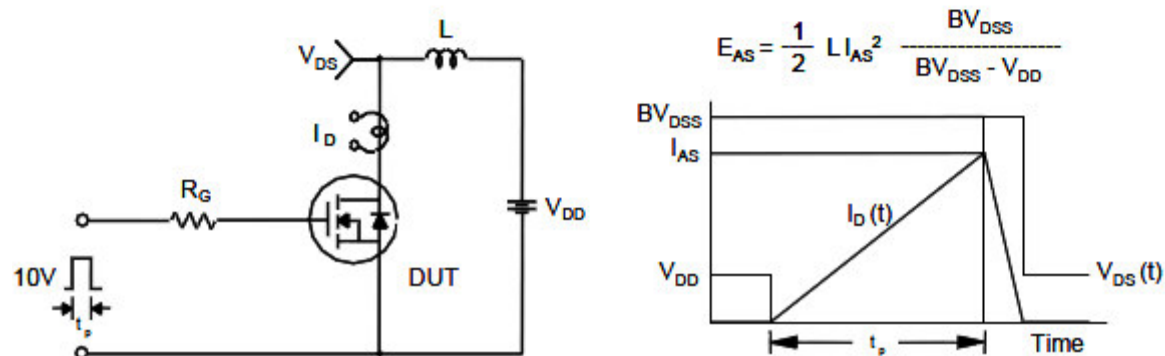
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

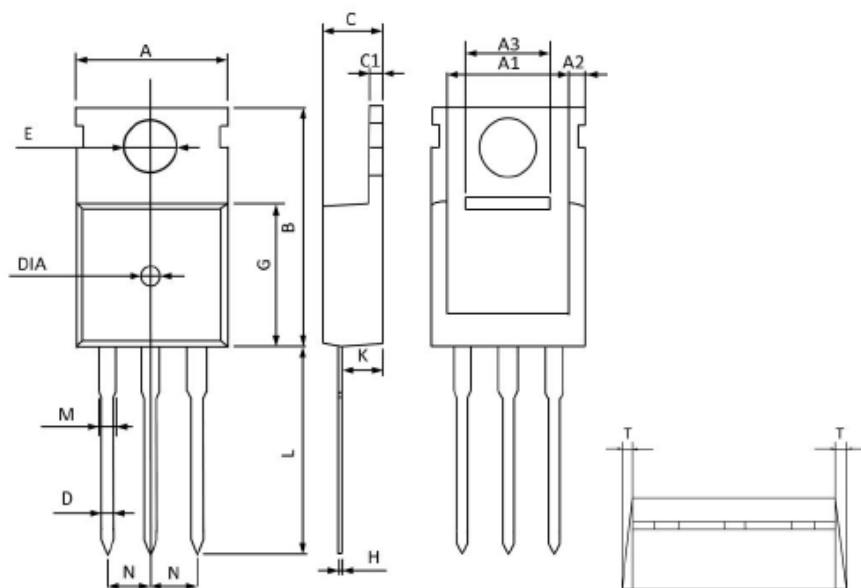


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

TO-220



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	9.70	10.30	0.382	0.406
A1	8.44	8.84	0.332	0.348
A2	1.05	1.25	0.041	0.049
A3	5.10	5.30	0.201	0.209
B	15.40	16.20	0.606	0.638
C	4.28	4.68	0.169	0.184
C1	1.10	1.50	0.043	0.059
D	0.60	1.00	0.024	0.039
E	3.40	3.80	0.134	0.150
G	8.70	9.30	0.343	0.366
H	0.40	0.60	0.016	0.024
K	2.10	2.70	0.083	0.106
L	12.80	13.60	0.504	0.535
M	1.10	1.50	0.043	0.059
N	2.49	2.59	0.098	0.102
T	W0.35		W0.014	
DIA	Deep0.2(TYP)	Φ 1.5(TYP)	Deep0.008(TYP)	Φ 0.059(TYP)

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd NeiHu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Shenzhen Branch(China)	
	1113 B Building, Happiness Washington, Baoan Nan Road, Luohu District, Shenzhen City, China
	0755-22208941
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587